

# < HIGH VOLTAGE DIODE MODULE >

## RM750DC-90X

HIGH POWER SWITCHING USE  
INSULATED TYPE

High Voltage Diode Modules

### RM750DC-90X



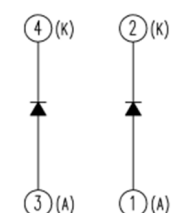
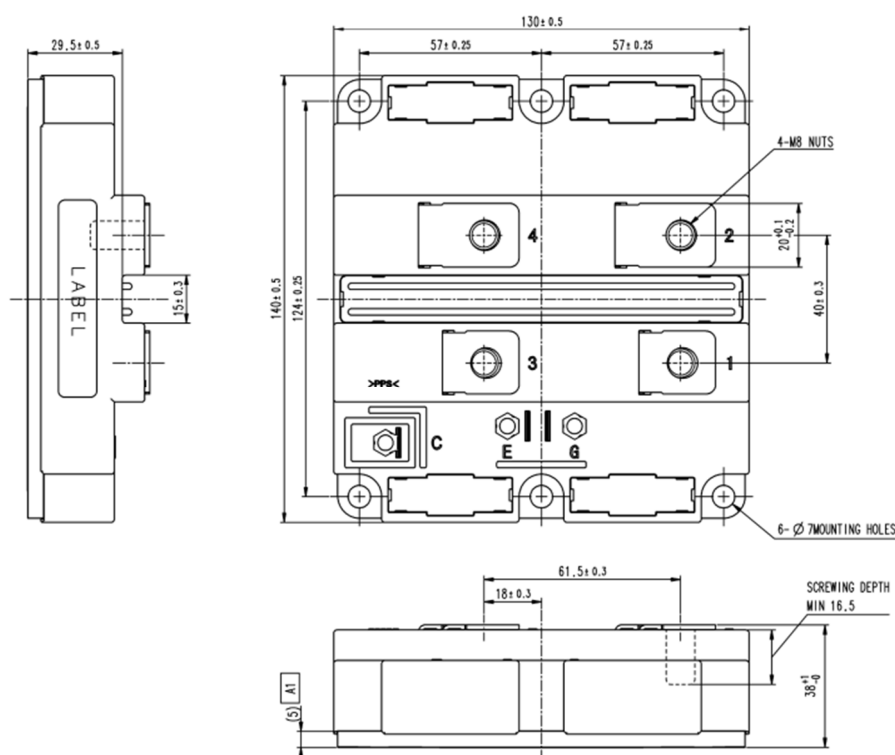
- $I_F$  ..... 2 x 750A
- $V_{RRM}$  ..... 4500V
- 2-element in a Pack
- RFC Diode
- AlSiC Baseplate

### APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers

### OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



接線図  
CIRCUIT DIAGRAM

**RM750DC-90X**HIGH POWER SWITCHING USE  
INSULATED TYPE**MAXIMUM RATINGS**

Item	Symbol	Conditions	Ratings	Unit
Repetitive peak reverse voltage	$V_{RRM}$	$T_J = -40...+150\text{ }^{\circ}\text{C}$	4500	V
		$T_J = -50\text{ }^{\circ}\text{C}$	4400	
Non-repetitive peak reverse voltage	$V_{RSM}$	$T_J = -40...+150\text{ }^{\circ}\text{C}$	4500	V
		$T_J = -50\text{ }^{\circ}\text{C}$	4400	
Forward current	$I_F$	DC, $T_c = 85\text{ }^{\circ}\text{C}$	750	A
Repetitive peak forward current	$I_{FRM}$	Pulse	1500	A
Isolation voltage	$V_{iso}$	RMS, sinusoidal, $f = 60\text{ Hz}$ , $t = 1\text{ min}$	6000	V
Partial discharge charge	$Q_{PD}$	Charged part to the baseplate RMS sinusoidal, 60 Hz 1 min, $T_c = 25\text{ }^{\circ}\text{C}$ $V_1 = 4800\text{ V}_{rms}$ , $V_2 = 3500\text{ V}_{rms}$ (acc. to IEC 61287-1)	10	pC
Junction temperature	$T_J$	-	$-50 \sim +150$	$^{\circ}\text{C}$
Storage temperature	$T_{stg}$	-	$-55 \sim +150$	$^{\circ}\text{C}$
Operating junction temperature	$T_{jop}$	-	$-50 \sim +150$	$^{\circ}\text{C}$
Reverse recovery power dissipation	$P_{rr}$	$V_{CC} \leq 3400\text{ V}$ , $L_S \leq 200\text{ nH}$ , $I_F \leq 1500\text{ A}$ , $di_{on}/dt \leq 3300\text{ A}/\mu\text{s}$ , $T_J = 150\text{ }^{\circ}\text{C}$	2.0	MW
Non-repetitive surge forward current	$I_{FSM}$	$T_{J\_start} = 150\text{ }^{\circ}\text{C}$ , $t_p = 10\text{ ms}$ , Half-sine	6.7	kA
Surge current load integral	$I^2t$	wave, $V_R = 0\text{ V}$	224	$\text{kA}^2\text{s}$

**ELECTRICAL CHARACTERISTICS**

Item	Symbol	Conditions		Limits			Unit
				Min.	Typ.	Max.	
Repetitive reverse current	I <sub>RRM</sub>	V <sub>RM</sub> = V <sub>RRM</sub>	T <sub>j</sub> = 25°C	—	—	1.5	mA
			T <sub>j</sub> = 125°C	—	1.5	—	
			T <sub>j</sub> = 150°C	—	—	15.0	
Forward voltage	V <sub>FM</sub> (Terminal )	I <sub>F</sub> = 750 A	T <sub>j</sub> = 25°C	—	2.55	—	V
			T <sub>j</sub> = 125°C	—	3.15	—	
			T <sub>j</sub> = 150°C	—	3.30	—	
Forward voltage	V <sub>FM</sub> (Chip)	I <sub>F</sub> = 750 A	T <sub>j</sub> = 25°C	—	2.35	—	V
			T <sub>j</sub> = 125°C	—	2.90	—	
			T <sub>j</sub> = 150°C	—	3.00	3.50	
Reverse recovery time	t <sub>rr</sub>	V <sub>CC</sub> = 2800 V I <sub>F</sub> = 750 A L <sub>S</sub> = 200 nH  -di <sub>F</sub> /dt ≅ 3300 A/μs @ T <sub>j</sub> = 25°C 2920A/μs @ T <sub>j</sub> = 125°C 2710A/μs @ T <sub>j</sub> = 150°C	T <sub>j</sub> = 25°C	—	—	—	μs
			T <sub>j</sub> = 125°C	—	1.50	—	
			T <sub>j</sub> = 150°C	—	1.70	—	
Reverse recovery current	I <sub>rr</sub>		T <sub>j</sub> = 25°C	—	—	—	A
			T <sub>j</sub> = 125°C	—	1080	—	
			T <sub>j</sub> = 150°C	—	1080	—	
Reverse recovery charge <sup>(Note 1)</sup>	Q <sub>rr(10%)</sub>		T <sub>j</sub> = 25°C	—	—	—	μC
			T <sub>j</sub> = 125°C	—	1530	—	
			T <sub>j</sub> = 150°C	—	1560	—	
Reverse recovery charge	Q <sub>rr</sub>		T <sub>j</sub> = 25°C	—	—	—	μC
			T <sub>j</sub> = 125°C	—	1590	—	
			T <sub>j</sub> = 150°C	—	1620	—	

**ELECTRICAL CHARACTERISTICS**

Item	Symbol	Conditions		Limits			Unit
				Min.	Min.	Min.	
Reverse recovery energy per pulse (Note 2)	E <sub>rec</sub> (10%)	V <sub>CC</sub> = 2800 V I <sub>F</sub> = 750 A L <sub>S</sub> = 200 nH	T <sub>J</sub> = 25°C	—	1.85	—	J
			T <sub>J</sub> = 125°C	—	2.40	—	
			T <sub>J</sub> = 150°C	—	2.45	—	
Reverse recovery energy per pulse	E <sub>rec</sub>	-di <sub>F</sub> /dt ≅ 3300 A/μs @ T <sub>J</sub> = 25°C 2920A/μs @ T <sub>J</sub> = 125°C 2710A/μs @ T <sub>J</sub> = 150°C	T <sub>J</sub> = 25°C	—	1.90	—	J
			T <sub>J</sub> = 125°C	—	2.55	—	
			T <sub>J</sub> = 150°C	—	2.60	—	

**THERMAL CHARACTERISTICS**

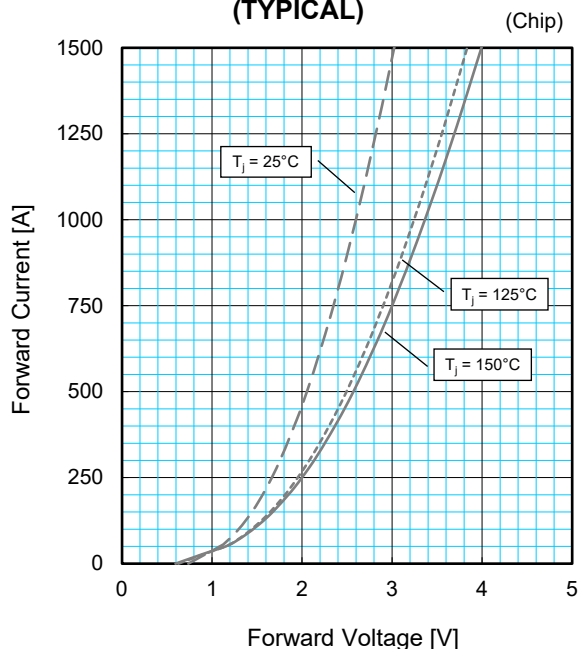
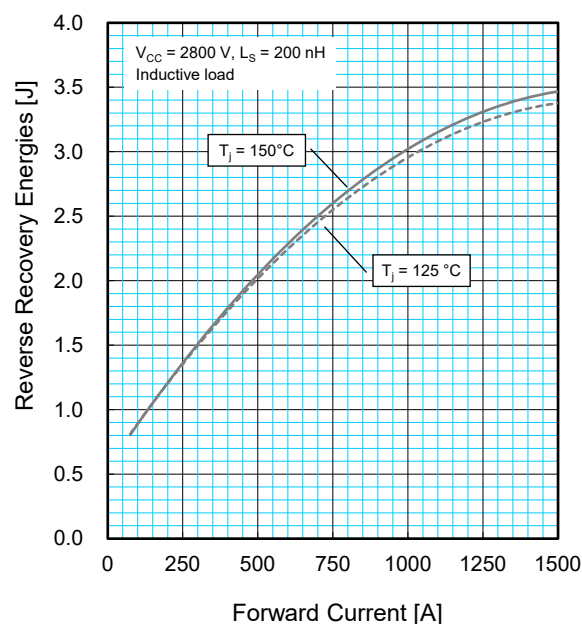
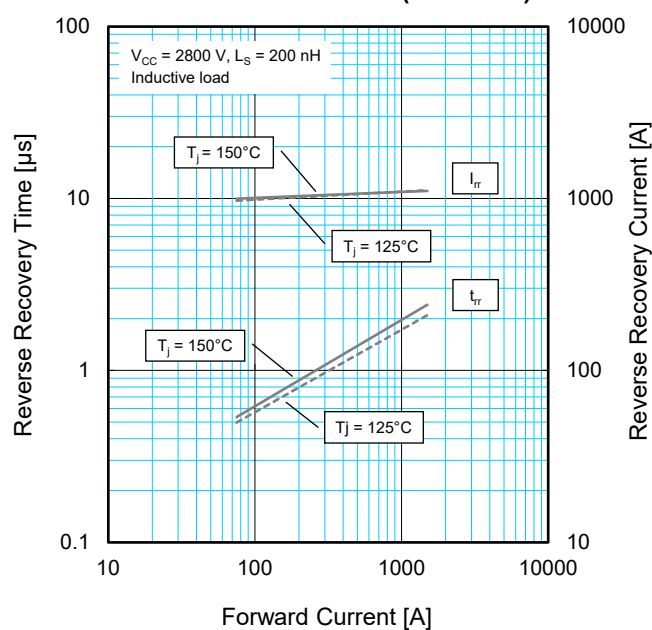
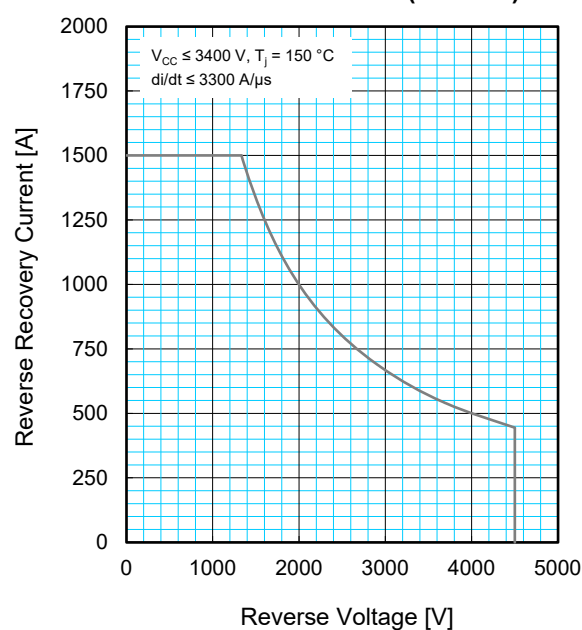
Item	Symbol	Conditions	Limits			Unit
			Min.	Typ.	Max.	
Thermal resistance	$R_{th(j-c)}$	Junction to Case, 1/2 module	—	—	23.4	K/kW
Contact thermal resistance	$R_{th(c-s)}$	Case to heat sink, 1/2 module $\lambda_{grease} = 1\text{ W/m}\cdot\text{K}$ , $D_{(c-s)} = 80\text{ }\mu\text{m}$	—	15.0	—	K/kW

**MECHANICAL CHARACTERISTICS**

Item	Symbol	Conditions	Limits			Unit
			Min.	Typ.	Max.	
Mounting torque	$M_t$	Main terminals screw: M8	7.0	—	19.0	N·m
	$M_s$	Mounting screw: M6	3.0	—	6.0	N·m
Mass	$m$	—	—	0.9	—	kg
Comparative tracking index	CTI	—	600	—	—	—
Clearance distance in air	$d_a$	Anode terminal – Cathode terminal	19.5	—	—	mm
Creepage distance along surface	$d_s$	Anode terminal – Cathode terminal	32.0	—	—	mm
Internal inductance	$L_{P(A-K)}$	$T_c = 25^\circ\text{C}$ , 1/2 module	—	24	—	nH
Internal lead resistance	$R_{AA'+KK'}$	$T_c = 25^\circ\text{C}$ , 1/2 module	—	0.27	—	m $\Omega$

Note 1.  $Q_{rr(10\%)}$  is the integral of  $I_{rr} \times dt(t(0.1I_F) - t(-0.1I_F))$ .

Note 2.  $E_{rec(10\%)}$  is the integral of  $0.1V_R \times 0.1I_F \times dt$ .

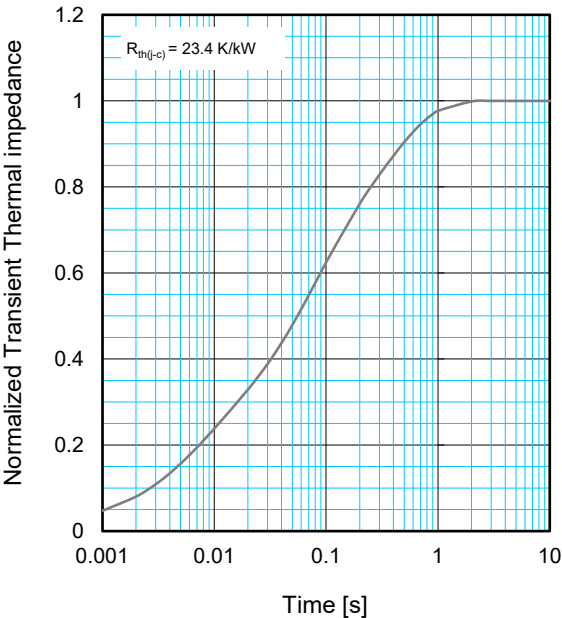
**RM750DC-90X**HIGH POWER SWITCHING USE  
INSULATED TYPE**PERFORMANCE CURVES****FORWARD CHARACTERISTICS  
(TYPICAL)****REVERSE RECOVERY ENERGY  
CHARACTERISTICS (TYPICAL)****REVERSE RECOVERY  
CHARACTERISTICS (TYPICAL)****REVERSE RECOVERY  
SAFE OPERATING AREA (RRSOA)**

RM750DC-90X

HIGH POWER SWITCHING USE  
INSULATED TYPE

PERFORMANCE CURVES

TRANSIENT THERMAL IMPEDANCE  
CHARACTERISTICS



$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i \left\{ 1 - \exp\left(-\frac{t}{\tau_i}\right) \right\}$$

	1	2	3	4
$R_i / R_{th(j-c)}$	0.0096	0.1893	0.4044	0.3967
$\tau_i$ [s]	0.0001	0.0058	0.0602	0.3512

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